

IN THE SUBSTITUTE SPECIFICATION

Please replace the paragraph of the substitute specification beginning at page 5, line 2, with:

According to a most preferable variant, drying, removing physically adsorbed substances from the first and second wafer surfaces, joining the wafers, their splicing and exfoliating of the first wafer are carried out in the low vacuum ($10^1 - 10^4$ Pa) at moderate temperatures, i.e., 80°C or above, most preferably the temperature interval from 80° to 350°C for 0.1 to 100 hours.